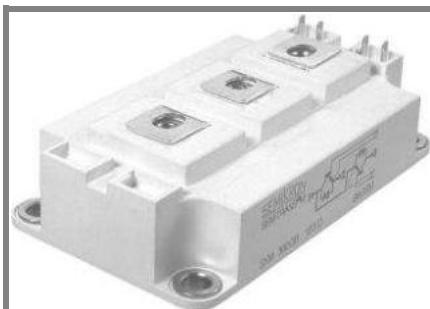




SEMITRANS® 3

Ultra Fast IGBT Modules

SKM 400GB125D

SKM 400GAL125D

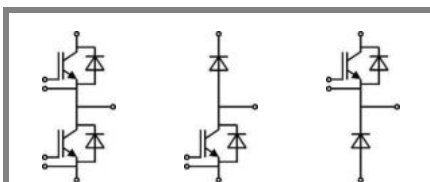
SKM 400GAR125D

Features

- Low inductance case
- Short tail current with low temperature dependence
- High short circuit capability, self limiting to $6 \times I_{Cnom}$
- Fast & soft inverse CAL diodes
- Isolated copper baseplate using DBC Direct Copper Bonding Technology
- Large clearance (13 mm) and creepage distances (20 mm)

Typical Applications*

- Switched mode power supplies at $f_{sw} > 20\text{kHz}$
- Resonant inverters up to 100 kHz
- Inductive heating
- Electronic welders at $f_{sw} > 20\text{ kHz}$



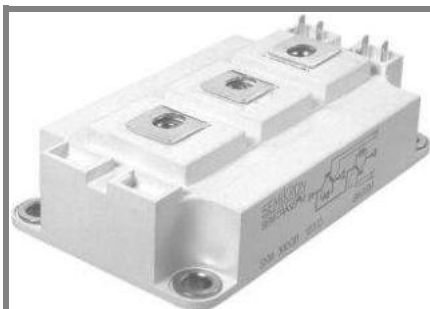
GB

GAL

GAR

Absolute Maximum Ratings			$T_c = 25\text{ }^{\circ}\text{C}$, unless otherwise specified	
Symbol	Conditions		Values	Units
IGBT				
V_{CES}	$T_j = 25\text{ }^{\circ}\text{C}$		1200	V
I_C	$T_j = 150\text{ }^{\circ}\text{C}$	$T_{case} = 25\text{ }^{\circ}\text{C}$	400	A
		$T_{case} = 80\text{ }^{\circ}\text{C}$	300	A
I_{CRM}	$I_{CRM}=2xI_{Cnom}$		600	A
V_{GES}			± 20	V
t_{psc}	$V_{CC} = 600\text{ V}; V_{GE} \leq 20\text{ V}; T_j = 125\text{ }^{\circ}\text{C}$ $V_{CES} < 1200\text{ V}$		10	μs
Inverse Diode				
I_F	$T_j = 150\text{ }^{\circ}\text{C}$	$T_{case} = 25\text{ }^{\circ}\text{C}$	390	A
		$T_{case} = 80\text{ }^{\circ}\text{C}$	260	A
I_{FRM}	$I_{FRM}=2xI_{Fnom}$		600	A
I_{FSM}	$t_p = 10\text{ ms}; \sin.$	$T_j = 150\text{ }^{\circ}\text{C}$	2880	A
Freewheeling Diode				
I_F	$T_j = 150\text{ }^{\circ}\text{C}$	$T_{case} = 25\text{ }^{\circ}\text{C}$	390	A
		$T_{case} = 80\text{ }^{\circ}\text{C}$	260	A
I_{FRM}	$I_{FRM}=2xI_{Fnom}$		600	A
I_{FSM}	$t_p = 10\text{ ms}; \sin.$	$T_j = 150\text{ }^{\circ}\text{C}$	2880	A
Module				
$I_{t(RMS)}$			500	A
T_{vj}			- 40...+ 150	$^{\circ}\text{C}$
T_{stg}			- 40...+ 125	$^{\circ}\text{C}$
V_{isol}	AC, 1 min.		4000	V

Characteristics			T _c = 25 °C, unless otherwise specified				
Symbol	Conditions		min.	typ.	max.	Units	
IGBT							
V _{GE(th)}	V _{GE} = V _{CE} , I _C = 12 mA		4,5	5,5	6,5	V	
I _{CES}	V _{GE} = 0 V, V _{CE} = V _{CES} T _j = 25 °C			0,15	0,45	mA	
V _{CE0}				T _j = 25 °C	1,4	V	
				T _j = 125 °C	1,7	V	
r _{CE}	V _{GE} = 15 V			T _j = 25°C	6,3	mΩ	
				T _j = 125°C	7,6	mΩ	
V _{CE(sat)}	I _{Cnom} = 300 A, V _{GE} = 15 V			T _j = 25°C _{chiplev.}	3,3	3,85	V
				T _j = 125°C _{chiplev.}	4	4,55	V
C _{ies}	V _{CE} = 25, V _{GE} = 0 V f = 1 MHz				22	30	nF
C _{oes}					3,3	4	nF
C _{res}					1,2	1,6	nF
Q _G	V _{GE} = 0V - +20V				2650		nC
R _{Gint}	T _j = °C				1,25		Ω
t _{d(on)}	R _{Gon} = 2 Ω		V _{CC} = 600V I _C = 300A		70		ns
t _r					50		ns
E _{on}					17		mJ
t _{d(off)}	R _{Goff} = 2 Ω		T _j = 125 °C V _{GE} = ±15V		500		ns
t _f					32		ns
E _{off}					18		mJ
R _{th(j-c)}	per IGBT				0,05		K/W



SEMITRANS® 3

Ultra Fast IGBT Modules

SKM 400GB125D

SKM 400GAL125D

SKM 400GAR125D

Features

- Low inductance case
- Short tail current with low temperature dependence
- High short circuit capability, self limiting to $6 \times I_{cnom}$
- Fast & soft inverse CAL diodes
- Isolated copper baseplate using DBC Direct Copper Bonding Technology
- Large clearance (13 mm) and creepage distances (20 mm)

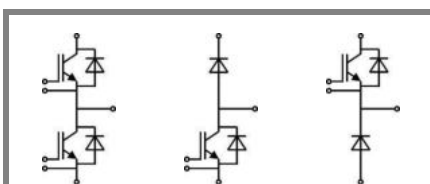
Typical Applications*

- Switched mode power supplies at $f_{sw} > 20\text{kHz}$
- Resonant inverters up to 100 kHz
- Inductive heating
- Electronic welders at $f_{sw} > 20\text{ kHz}$

Characteristics					
Symbol	Conditions	min.	typ.	max.	Units
Inverse Diode					
$V_F = V_{EC}$	$I_{Fnom} = 300\text{ A}; V_{GE} = 0\text{ V}$	$T_j = 25\text{ }^\circ\text{C}_{chiplev.}$	2	2,5	V
		$T_j = 125\text{ }^\circ\text{C}_{chiplev.}$	1,8		V
V_{F0}		$T_j = 25\text{ }^\circ\text{C}$	1,1	1,2	V
		$T_j = 125\text{ }^\circ\text{C}$			V
r_F		$T_j = 25\text{ }^\circ\text{C}$	3	4,3	mΩ
		$T_j = 125\text{ }^\circ\text{C}$			mΩ
I_{RRM}	$I_F = 300\text{ A}$	$T_j = 125\text{ }^\circ\text{C}$	350		A
Q_{rr}	$di/dt = 8300\text{ A}/\mu\text{s}$		45		μC
E_{rr}	$V_{GE} = 0\text{ V}; V_{CC} = 600\text{ V}$		16		mJ
$R_{th(j-c)D}$	per diode			0,125	K/W
Freewheeling Diode					
$V_F = V_{EC}$	$I_{Fnom} = 300\text{ A}; V_{GE} = 0\text{ V}$	$T_j = 25\text{ }^\circ\text{C}_{chiplev.}$	2	2,5	V
		$T_j = 125\text{ }^\circ\text{C}_{chiplev.}$	1,8		V
V_{F0}		$T_j = 25\text{ }^\circ\text{C}$	1,1	1,2	V
		$T_j = 125\text{ }^\circ\text{C}$			V
r_F		$T_j = 25\text{ }^\circ\text{C}$	3	4,3	V
		$T_j = 125\text{ }^\circ\text{C}$			V
I_{RRM}	$I_F = 300\text{ A}$	$T_j = 125\text{ }^\circ\text{C}$	350		A
Q_{rr}	$di/dt = 8300\text{ A}/\mu\text{s}$		45		μC
E_{rr}	$V_{GE} = 0\text{ V}; V_{CC} = 600\text{ V}$		16		mJ
$R_{th(j-c)FD}$	per diode			0,125	K/W
Module					
L_{CE}			15	20	nH
$R_{CC'+EE'}$	res., terminal-chip	$T_{case} = 25\text{ }^\circ\text{C}$	0,35		mΩ
		$T_{case} = 125\text{ }^\circ\text{C}$	0,5		mΩ
$R_{th(c-s)}$	per module			0,038	K/W
M_s	to heat sink M6		3	5	Nm
M_t	to terminals M6		2,5	5	Nm
w				325	g

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

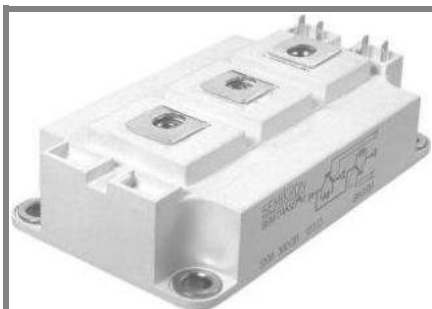
* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.



GB

GAL

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SEMITRANS® 3

Ultra Fast IGBT Modules

SKM 400GB125D

SKM 400GAL125D

SKM 400GAR125D

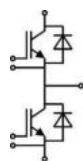
Features

- Low inductance case
- Short tail current with low temperature dependence
- High short circuit capability, self limiting to $6 \times I_{cnom}$
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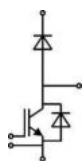
Typical Applications*

- Switched mode power supplies at $f_{sw} > 20\text{kHz}$
- Resonant inverters up to 100 kHz
- Inductive heating
- Electronic welders at $f_{sw} > 20\text{ kHz}$

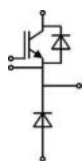
Z_{th} Symbol	Conditions	Values	Units
$Z_{th(j-c)I}$			
R_i	$i = 1$	36	mk/W
R_i	$i = 2$	10,5	mk/W
R_i	$i = 3$	3	mk/W
R_i	$i = 4$	0,5	mk/W
τ_{ui}	$i = 1$	0,0744	s
τ_{ui}	$i = 2$	0,0078	s
τ_{ui}	$i = 3$	0,0016	s
τ_{ui}	$i = 4$	0,0002	s
$Z_{th(j-c)D}$			
R_i	$i = 1$	75	mk/W
R_i	$i = 2$	38	mk/W
R_i	$i = 3$	10,6	mk/W
R_i	$i = 4$	1,4	mk/W
τ_{ui}	$i = 1$	0,0386	s
τ_{ui}	$i = 2$	0,0201	s
τ_{ui}	$i = 3$	0,001	s
τ_{ui}	$i = 4$	0,003	s



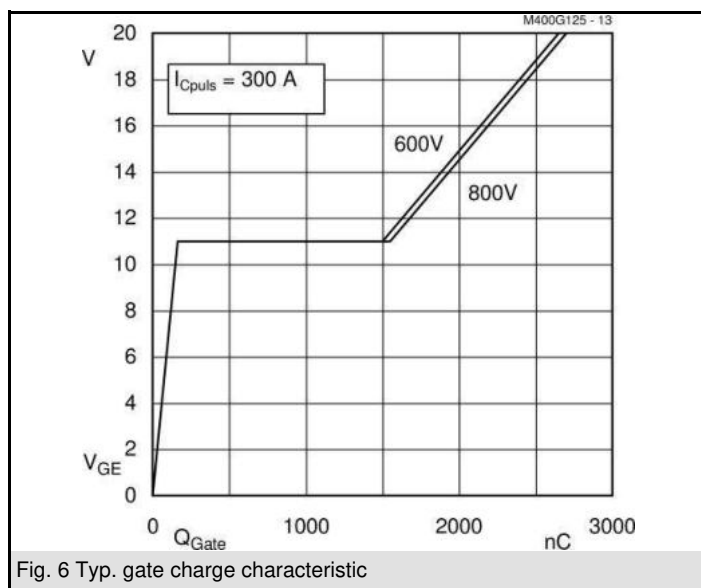
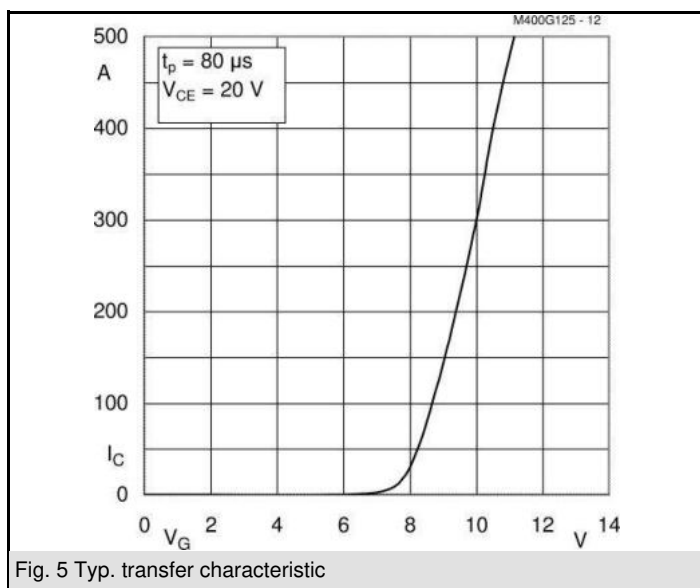
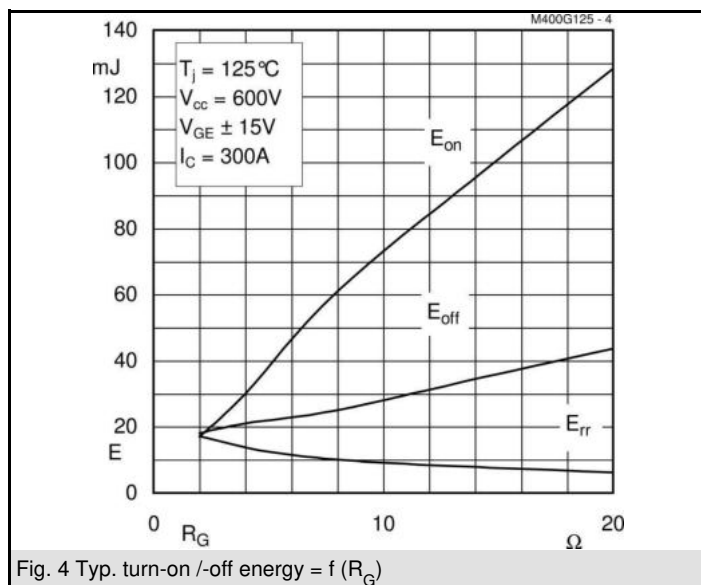
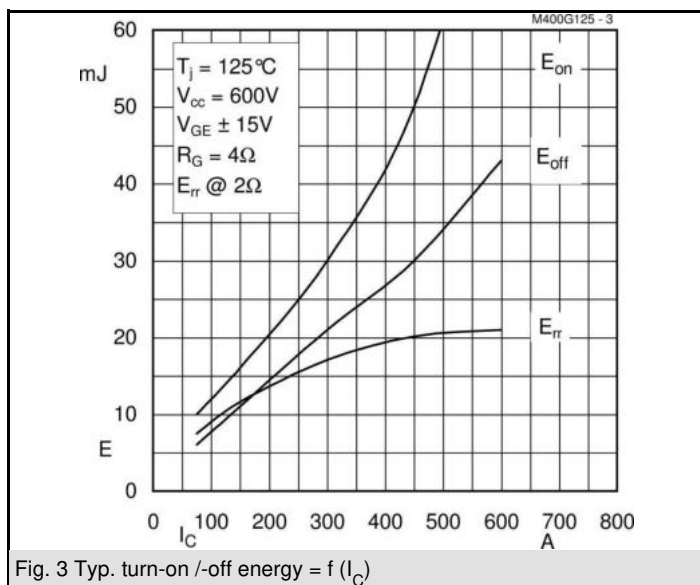
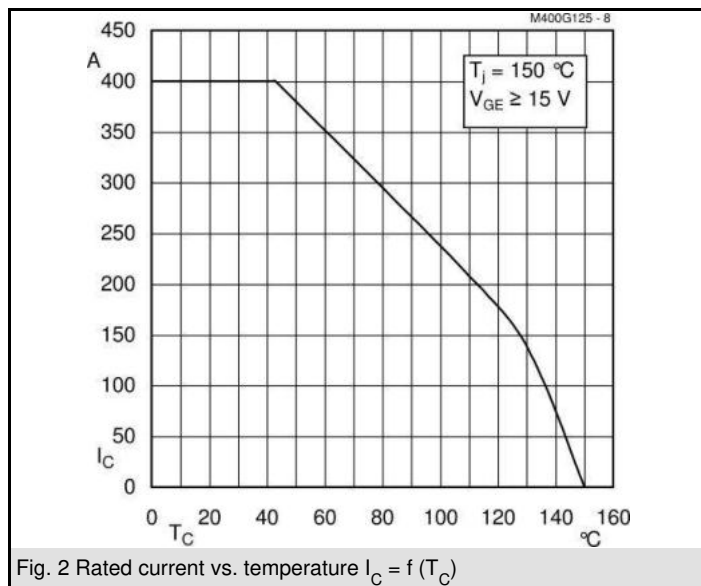
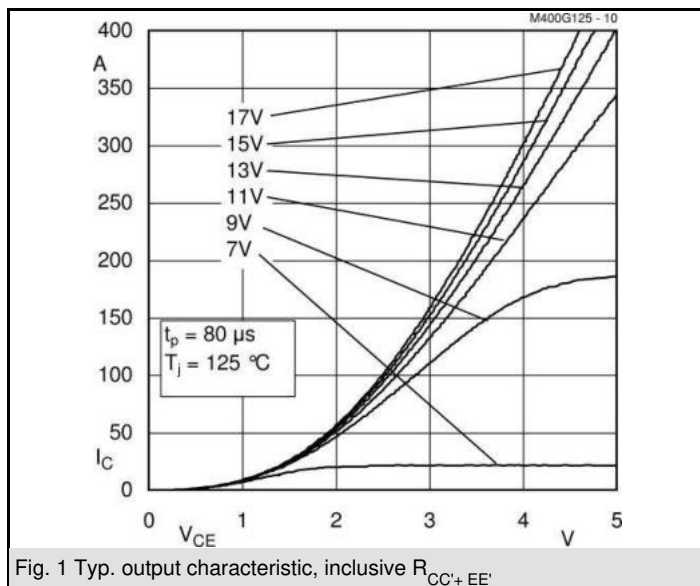
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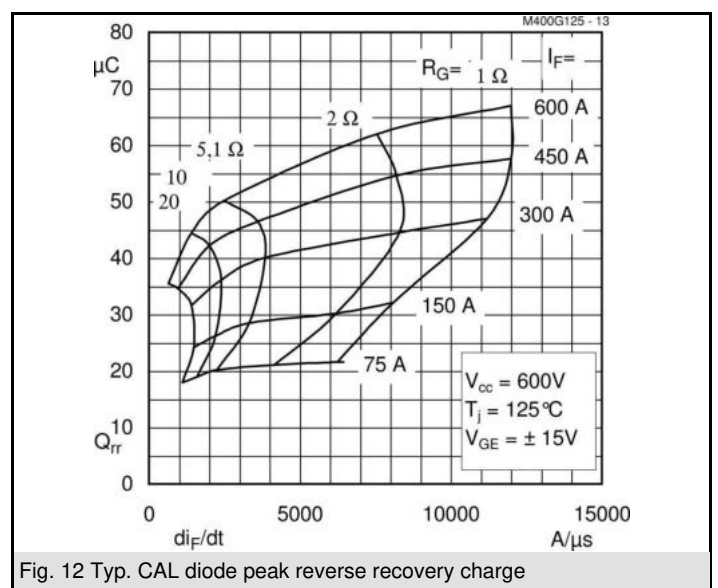
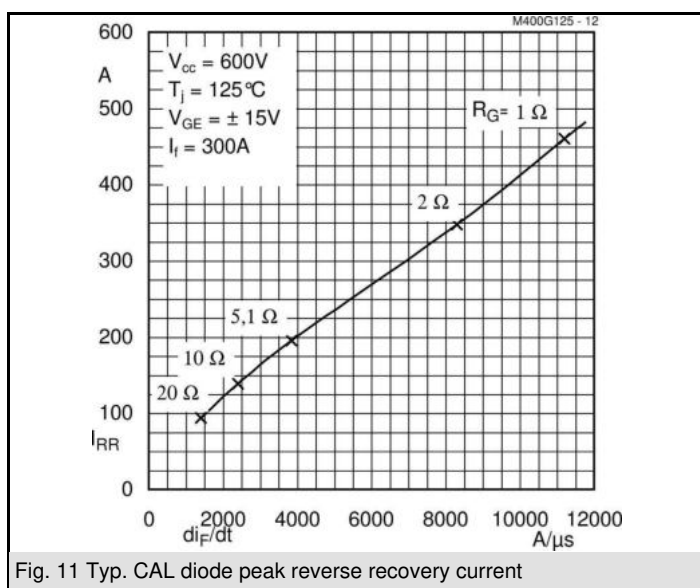
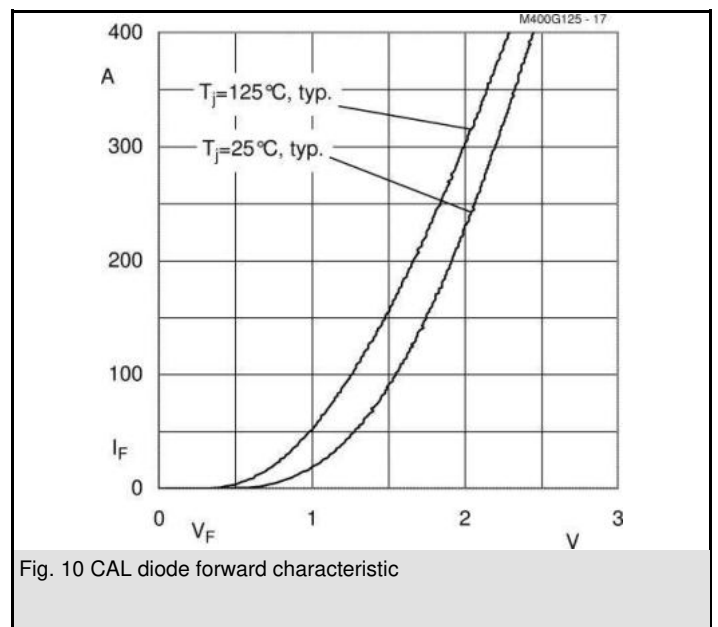
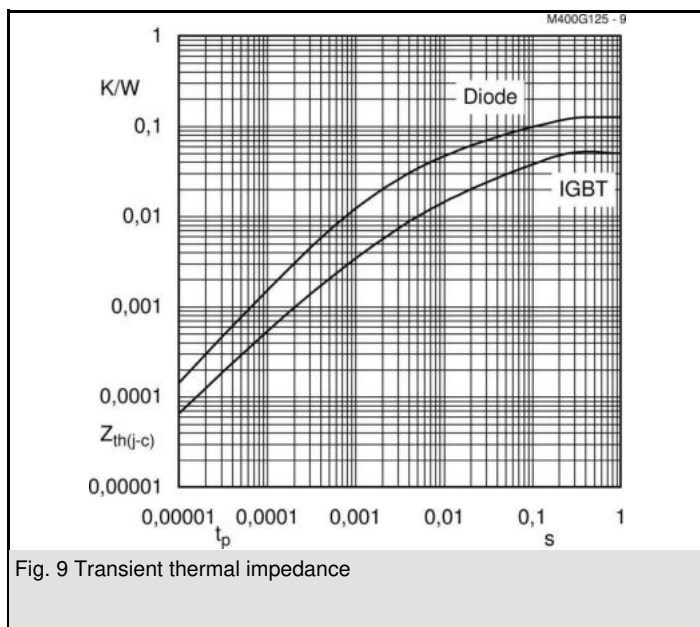
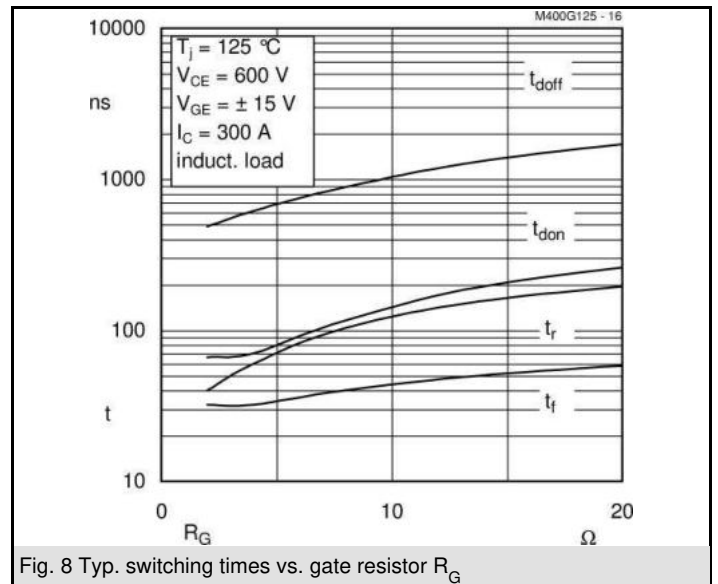
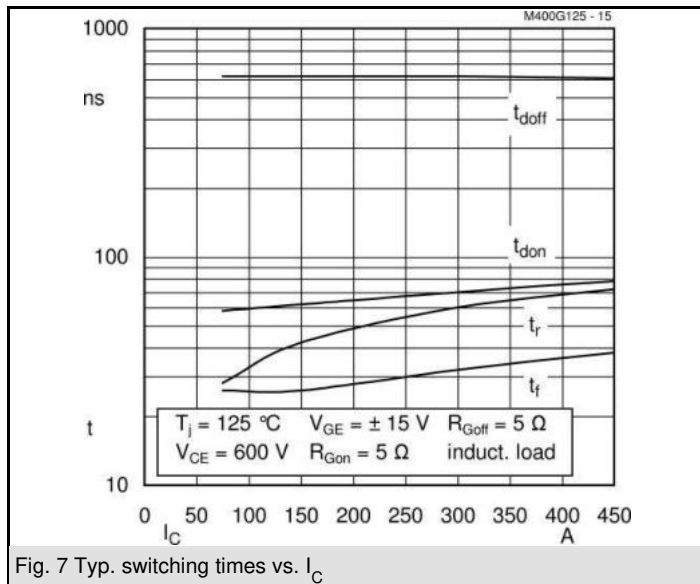


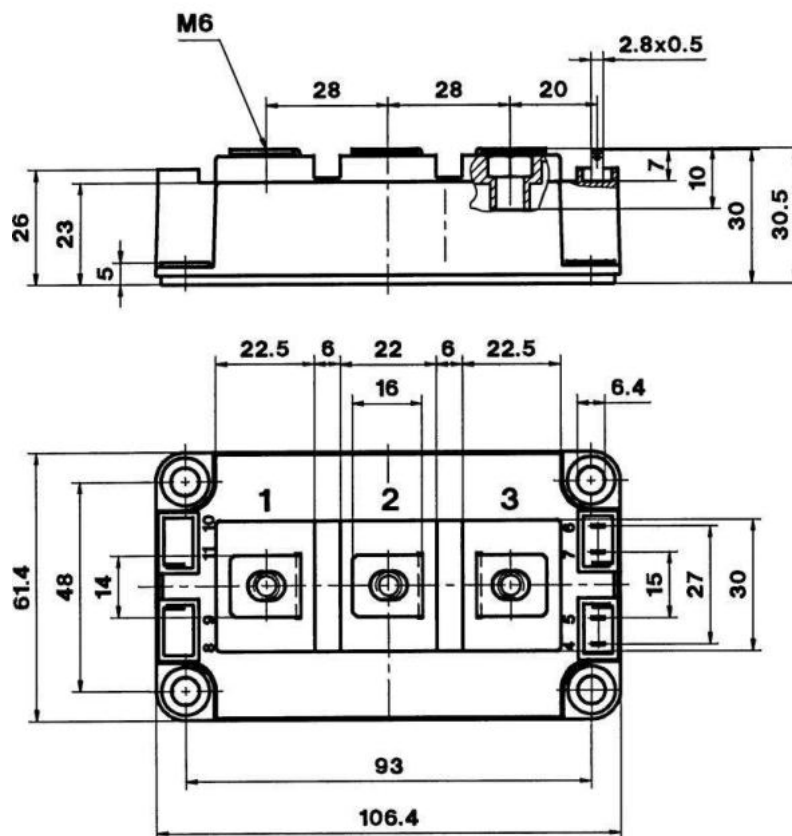
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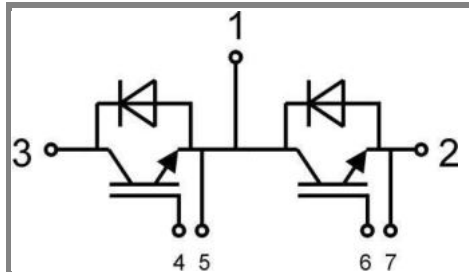
GAR





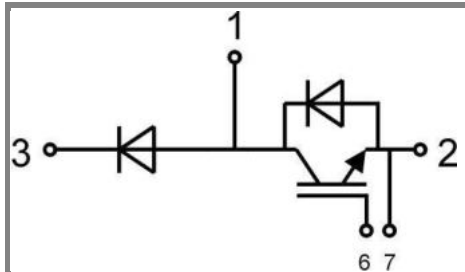


Case D 56



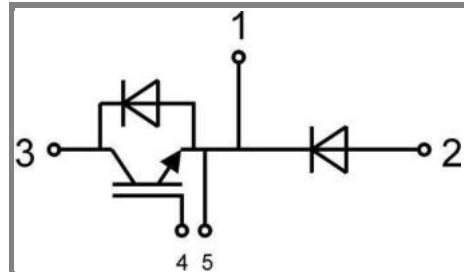
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Case D 56



GAL

Case D 57 (→ D 56)



GAR

Case D 58 (→ D 56)